

# H5N1503P

## Silicon N Channel MOS FET High Speed Power Switching

REJ03G0186-0100Z

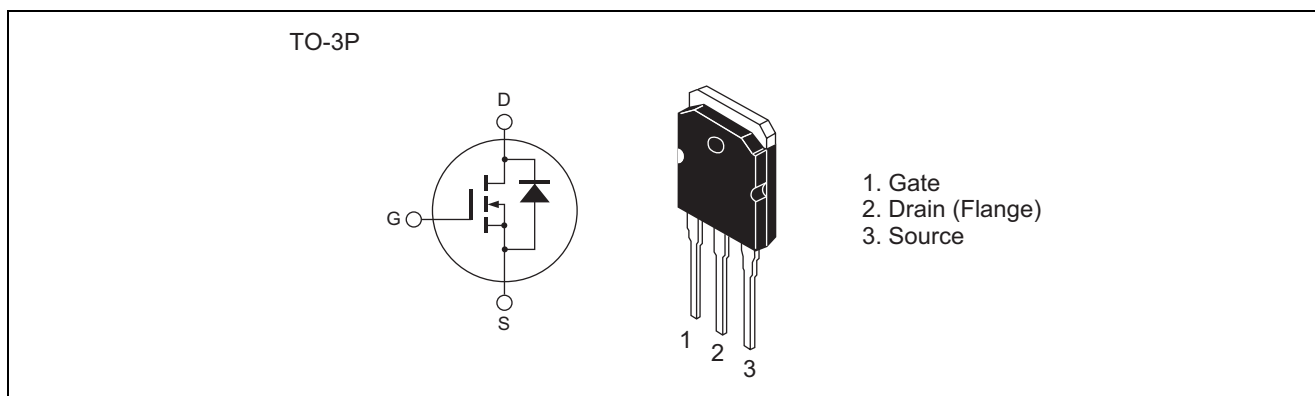
Rev.1.00

Mar.10.2004

### Features

- Low on-resistance
- Low leakage current
- High speed switching

### Outline



### Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to Source voltage	V <sub>DSS</sub>	150	V
Gate to Source voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub>	70	A
Drain peak current	I <sub>D (pulse)</sub> <sup>Note1</sup>	210	A
Body-Drain diode reverse Drain current	I <sub>DR</sub>	70	A
Avalanche current	I <sub>AP</sub> <sup>Note3</sup>	35	A
Avalanche energy	E <sub>AR</sub> <sup>Note3</sup>	91.8	mJ
Channel dissipation	P <sub>ch</sub> <sup>Note2</sup>	150	W
Channel to case thermal impedance	θ <sub>ch-c</sub>	0.833	°C/W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%  
 2. Value at T<sub>c</sub> = 25°C  
 3. ST<sub>ch</sub> = 25°C, T<sub>ch</sub> ≤ 150°C

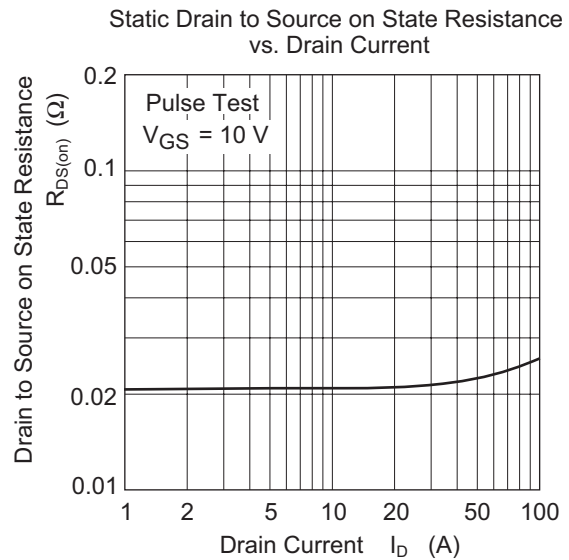
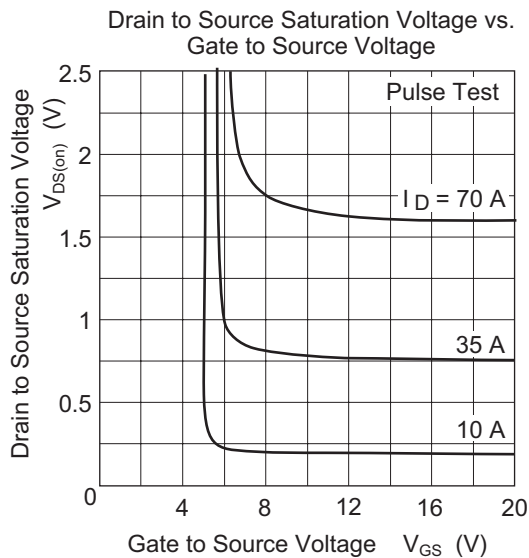
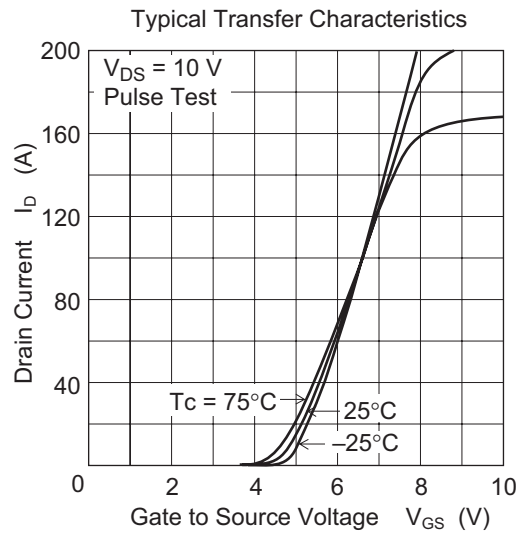
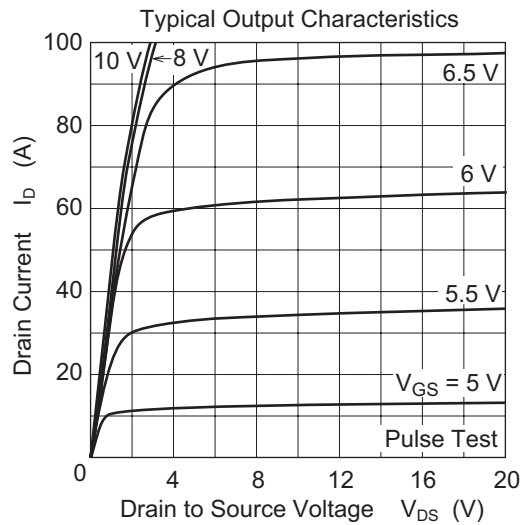
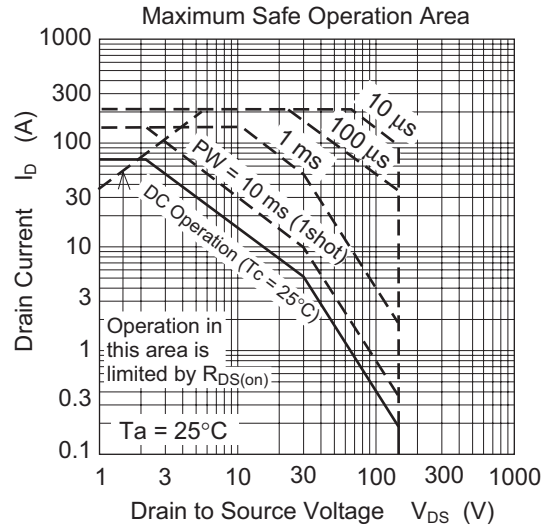
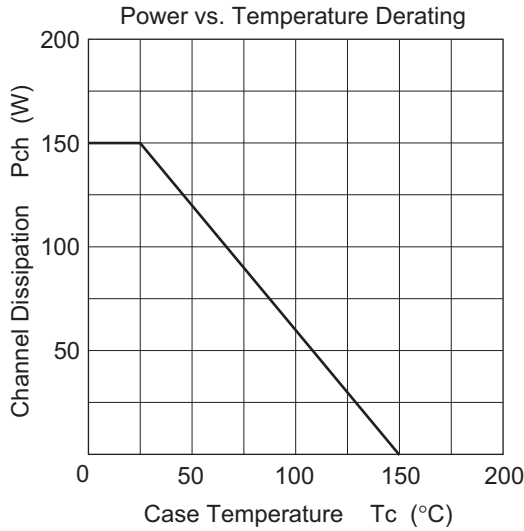
## Electrical Characteristics

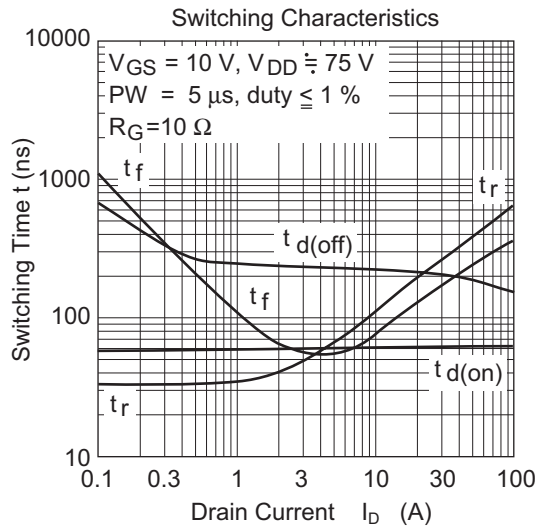
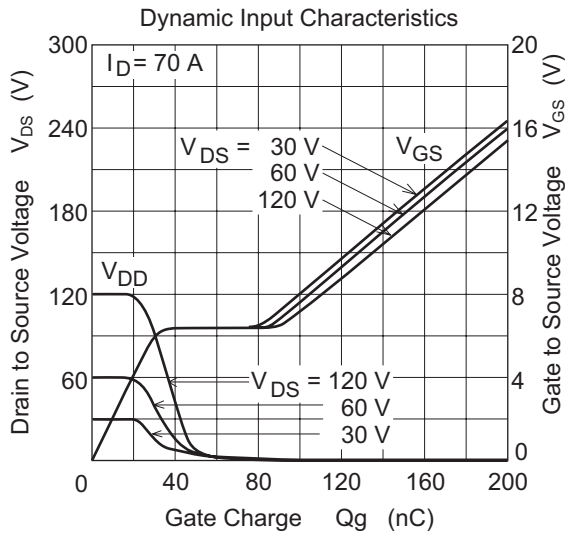
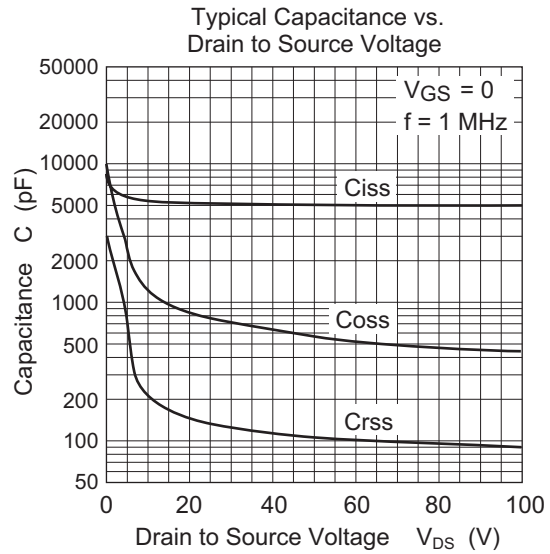
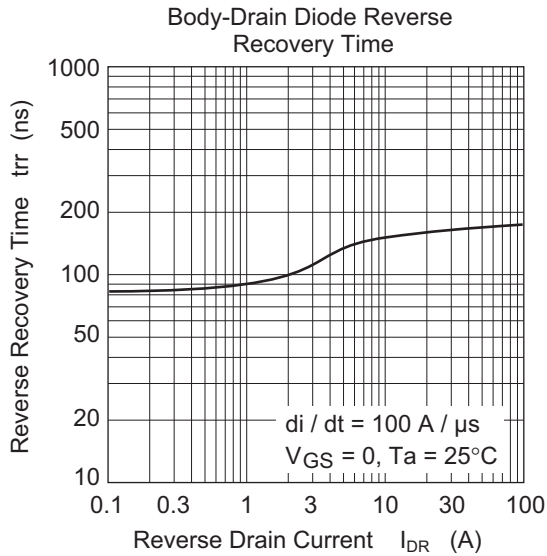
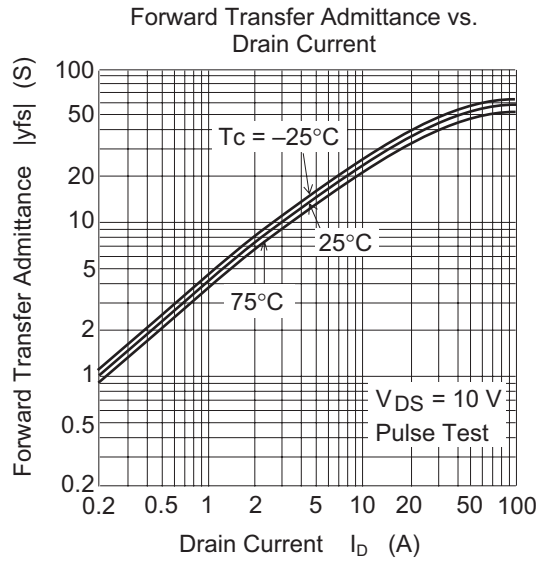
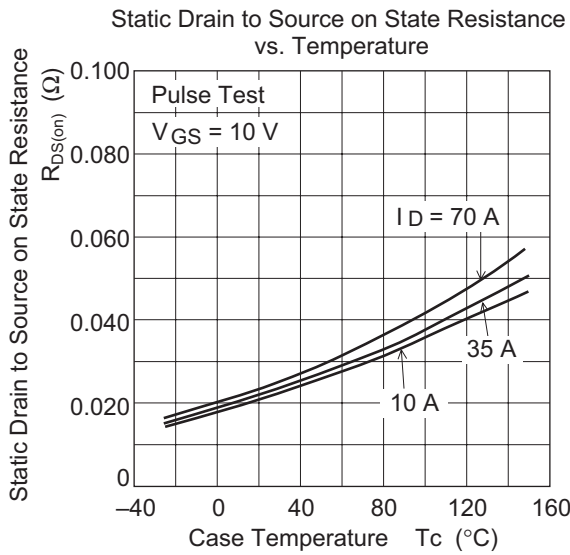
(Ta = 25°C)

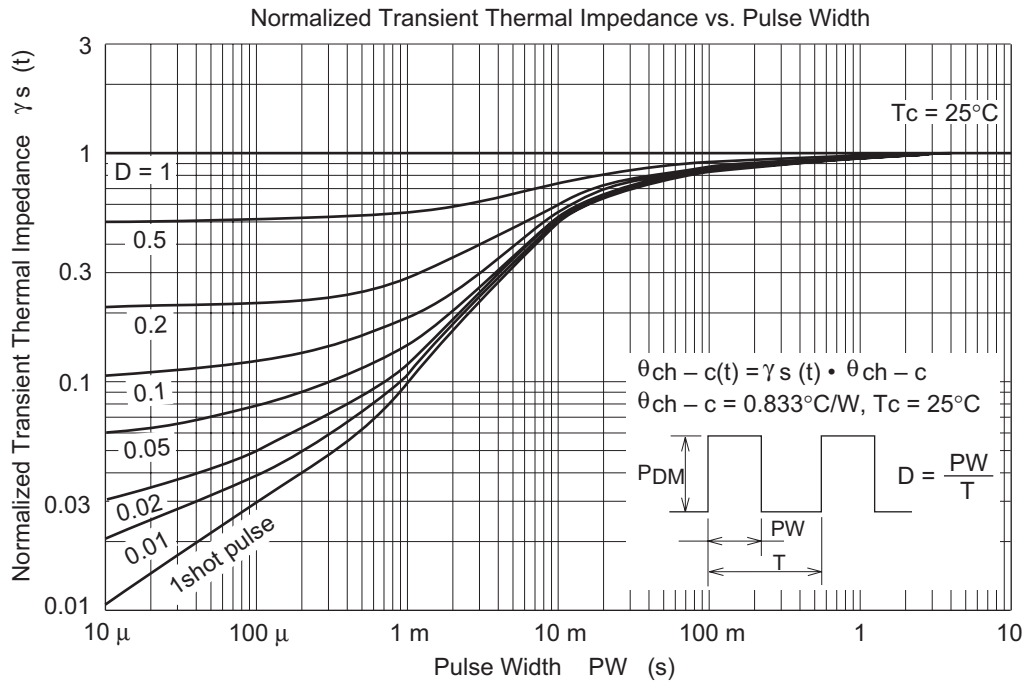
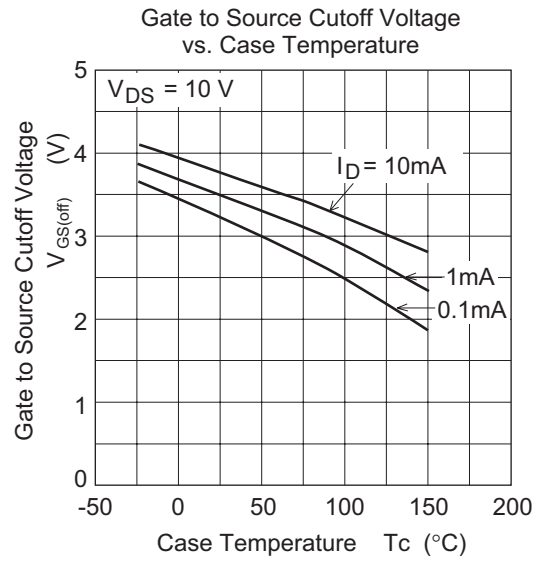
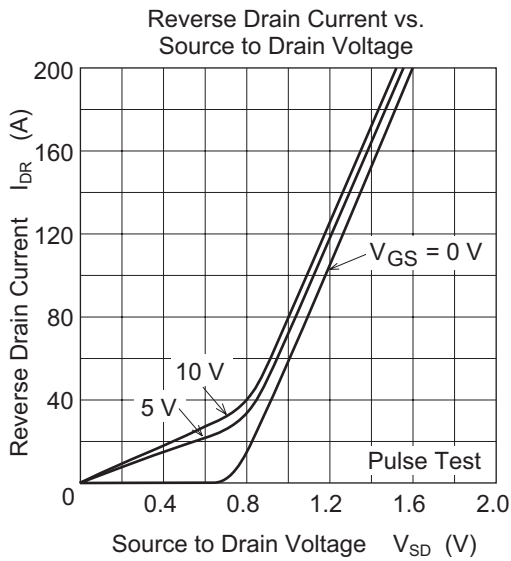
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to Source breakdown voltage	$V_{(BR)DSS}$	150	—	—	V	$I_D = 10 \text{ mA}$ , $V_{GS} = 0$
Zero Gate voltage drain current	$I_{DSS}$	—	—	1	$\mu\text{A}$	$V_{DS} = 150 \text{ V}$ , $V_{GS} = 0$
Gate to Source leak current	$I_{GSS}$	—	—	$\pm 0.1$	$\mu\text{A}$	$V_{GS} = \pm 30 \text{ V}$ , $V_{DS} = 0$
Gate to Source cutoff voltage	$V_{GS(off)}$	3.0	—	4.0	V	$V_{DS} = 10 \text{ V}$ , $I_D = 1 \text{ mA}$
Forward transfer admittance	$ y_{fs} $	27	46	—	S	$I_D = 35 \text{ A}$ , $V_{DS} = 10 \text{ V}$ <sup>Note4</sup>
Static Drain to Source on state resistance	$R_{DS(on)}$	—	0.022	0.027	$\Omega$	$I_D = 35 \text{ A}$ , $V_{GS} = 10 \text{ V}$ <sup>Note4</sup>
Input capacitance	$C_{iss}$	—	5100	—	pF	$V_{DS} = 25 \text{ V}$
Output capacitance	$C_{oss}$	—	770	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	$C_{rss}$	—	140	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	60	—	ns	$I_D = 35 \text{ A}$
Rise time	$t_r$	—	290	—	ns	$V_{GS} = 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	200	—	ns	$R_L = 2.14 \Omega$
Fall time	$t_f$	—	190	—	ns	$R_g = 10 \Omega$
Total Gate charge	$Q_g$	—	135	—	nC	$V_{DD} = 120 \text{ V}$
Gate to Source charge	$Q_{gs}$	—	30	—	nC	$V_{GS} = 10 \text{ V}$
Gate to Drain charge	$Q_{gd}$	—	60	—	nC	$I_D = 70 \text{ A}$
Body-Drain diode forward voltage	$V_{DF}$	—	1.1	1.7	V	$I_F = 70 \text{ A}$ , $V_{GS} = 0$ <sup>Note4</sup>
Body-Drain diode reverse recovery time	$t_{rr}$	—	180	—	ns	$I_F = 70 \text{ A}$ , $V_{GS} = 0$
Body-Drain diode reverse recovery charge	$Q_{rr}$	—	1.2	—	$\mu\text{C}$	$diF/dt = 100 \text{ A}/\mu\text{s}$

Notes: 4. Pulse test

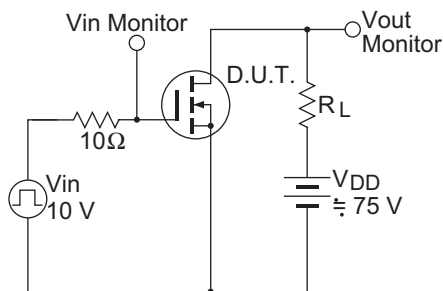
Main Characteristics



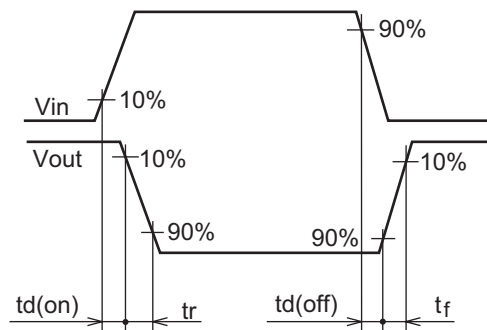




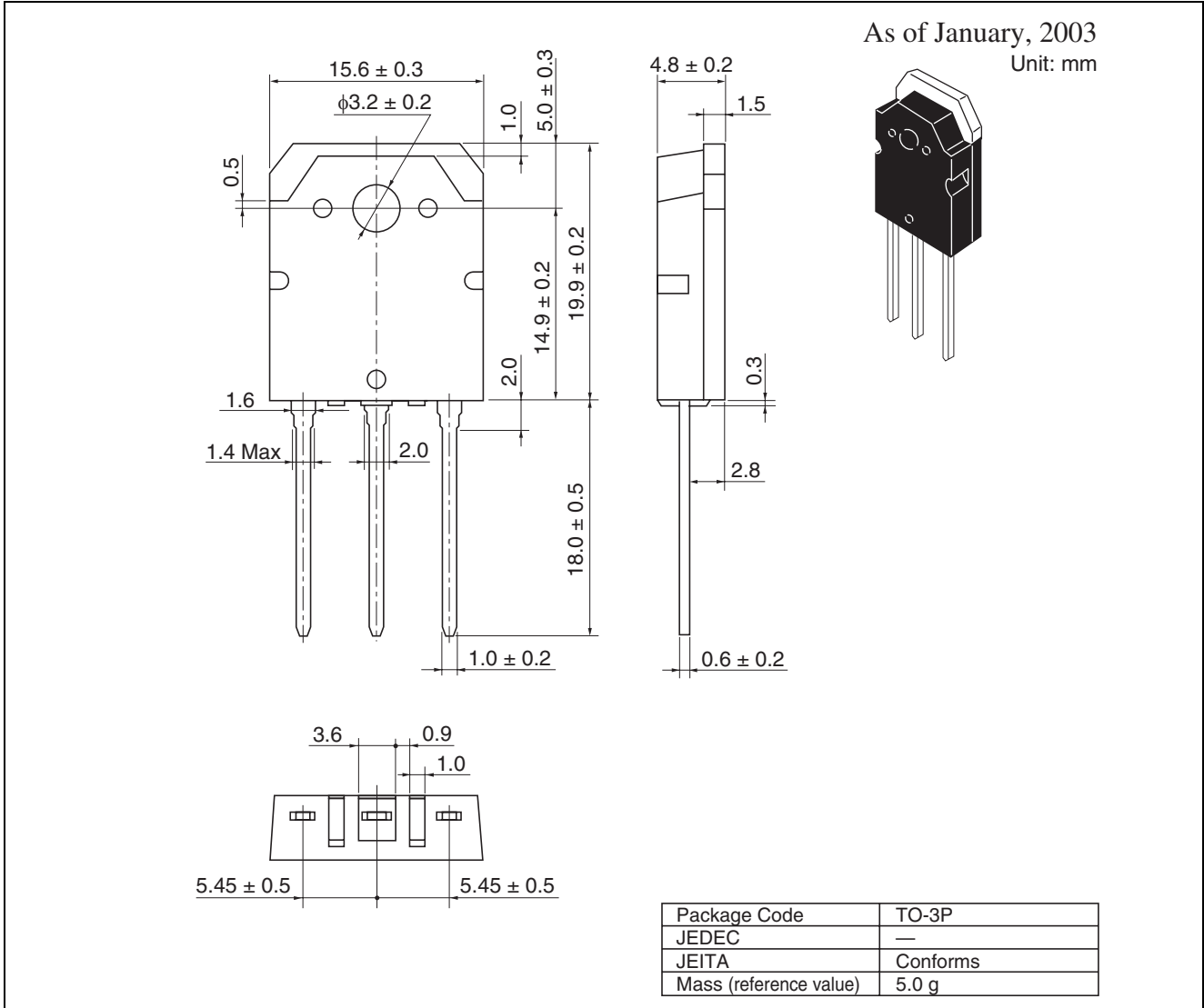
Switching Time Test Circuit



Waveform



Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
H5N1503P-E	30 pcs	Plastic magazine

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